

SANTA CLARA UNIVERSITY	ELEN 153 Fall 2017	Dr. S. Krishnan
Pre-Lab #2: The CMOS Inverter		

For the MOS devices in 90nm technology use the parameters listed below.

NMOS: $V_{tn0} = 0.39V$, $k_n' = 200\mu A/V^2$, $\gamma_n = 0$, $\lambda_n = 0$

PMOS: $V_{tp0} = 0.27V$, $k_p' = 60\mu A/V^2$, $\gamma_p = 0$, $\lambda_p = 0$

$V_{DD} = 1.2V$.

The $V_{IH} = 0.8V$ and $V_{IL} = 0.5V$.

- Draw the VTC for this inverter.
- Give the logic swing and noise margins for this inverter?
- What is the power consumed by this inverter:
 - when the input = 0V?
 - when the inverter drives the output from "0" to "1" with load capacitance of 1pF at a clock frequency of 100MHz.

